

PMF250XNEA 30 V, N-channel Trench MOSFET 17 March 2017

Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT323 (SC-70) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- · Low threshold voltage
- · Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM
- AEC-Q101 qualified

3. Applications

- · Relay driver
- · High-speed line driver
- Low-side loadswitch
- · Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	30	V
V_{GS}	gate-source voltage			-12	-	12	V
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	-	0.9	Α
Static characte	Static characteristics						
R _{DSon}	drain-source on-state resistance	V_{GS} = 4.5 V; I_D = 0.9 A; T_j = 25 °C		-	212	254	mΩ

^[1] Device mounted on an FR4 Printed Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	<u></u> 3	D
2	S	source		
3	D	drain	SC-70 (SOT323)	G S 017aaa255

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMF250XNEA	SC-70	plastic surface-mounted package; 3 leads	SOT323			

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PMF250XNEA	A3%

[1] % = placeholder for manufacturing site code

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	30	V
V _{GS}	gate-source voltage			-12	12	V
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	0.9	А
		V _{GS} = 4.5 V; T _{amb} = 100 °C	[1]	-	0.5	А
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	4	Α
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	$T_{j(init)}$ = 25 °C; I_D = 0.3 A; DUT in avalanche (unclamped)		-	2.5	mJ
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	275	mW
			[1]	-	342	mW
		T _{sp} = 25 °C		-	1.1	W
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain	diode			,		,
I _S	source current	T _{amb} = 25 °C	[1]	-	0.3	Α
ESD maximur	m rating					
V _{ESD}	electrostatic discharge voltage	НВМ		-	2000	V

^[1] Device mounted on an FR4 Printed Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².

^[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

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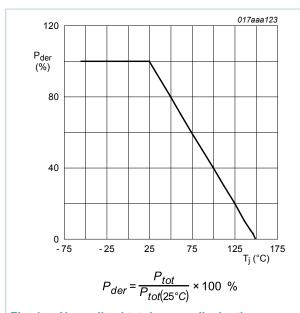


Fig. 1. Normalized total power dissipation as a function of junction temperature

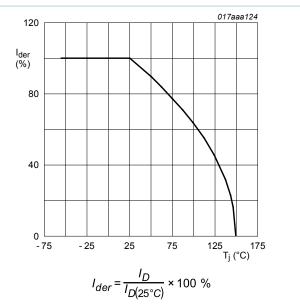


Fig. 2. Normalized continuous drain current as a function of junction temperature

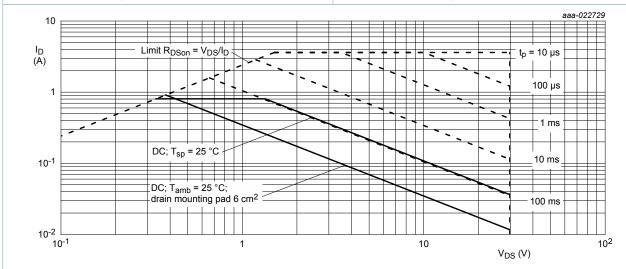


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient		[1]	-	397	457	K/W
			[2]	-	318	366	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	102	117	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

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[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm².

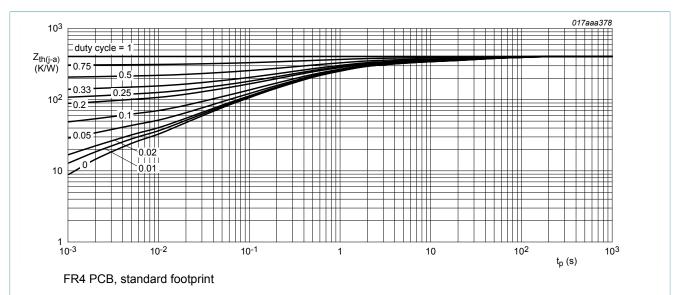


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

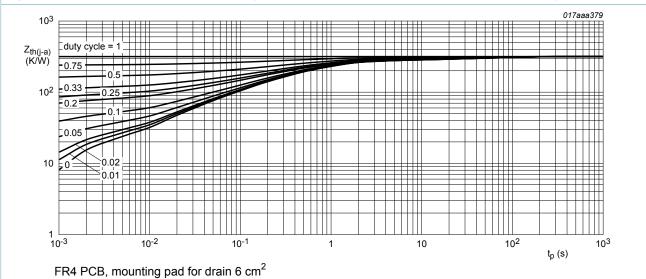


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
V _{(BR)DSS}	drain-source breakdown voltage	I_D = 250 μ A; V_{GS} = 0 V; T_j = 25 °C	30	-	-	V
V_{GSth}	gate-source threshold voltage	I _D = 250 μA; V _{DS} =V _{GS} ; T _j = 25 °C	0.75	1	1.25	V
I _{DSS}	drain leakage current	V _{DS} = 30 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μA
I _{GSS}	gate leakage current	V _{GS} = 12 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μA
		V _{GS} = -12 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μA
		V _{GS} = 4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	5	μA
		V _{GS} = -4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-5	μA
DOON	drain-source on-state	V_{GS} = 4.5 V; I_D = 0.9 A; T_j = 25 °C	-	212	254	mΩ
	resistance	V_{GS} = 4.5 V; I_D = 0.9 A; T_j = 150 °C	-	346	416	mΩ
		V_{GS} = 2.5 V; I_D = 0.8 A; T_j = 25 °C	-	269	321	mΩ
9 _{fs}	forward transconductance	V_{DS} = 10 V; I_D = 0.9 A; T_j = 25 °C	-	3.5	-	S
Dynamic c	haracteristics		,			
Q _{G(tot)}	total gate charge	$V_{DS} = 15 \text{ V}; I_D = 0.9 \text{ A}; V_{GS} = 4.5 \text{ V};$	-	1.05	1.65	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	0.15	-	nC
Q_{GD}	gate-drain charge		-	0.27	-	nC
C _{iss}	input capacitance	V _{DS} = 15 V; f = 1 MHz; V _{GS} = 0 V;	-	81	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	13	-	pF
C _{rss}	reverse transfer capacitance		-	8.5	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 15 V; I_D = 0.9 A; V_{GS} = 4.5 V;	-	7	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 ^{\circ}C$	-	14	-	ns
t _{d(off)}	turn-off delay time		-	17	-	ns
t _f	fall time		-	6	-	ns
Source-dra	in diode					
V_{SD}	source-drain voltage	I _S = 0.3 A; V _{GS} = 0 V; T _j = 25 °C	-	0.7	1.2	V

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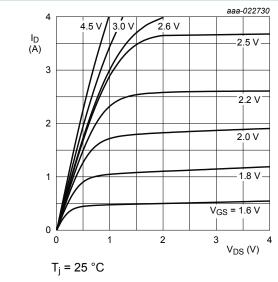


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

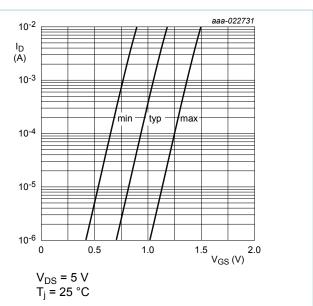


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

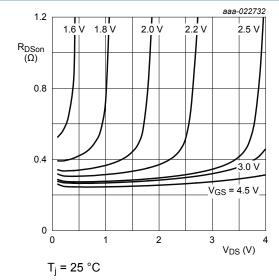


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

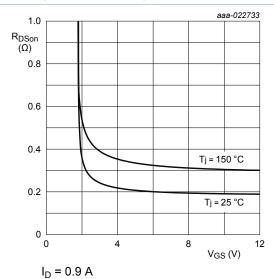


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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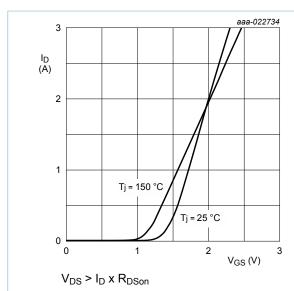


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

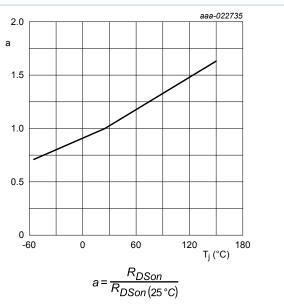


Fig. 11. Normalized drain-source on-state resistance as a function of ambient temperature; typical values

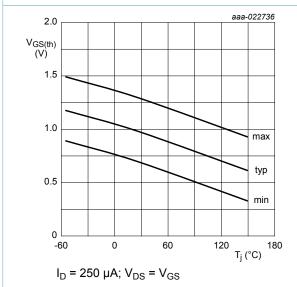


Fig. 12. Gate-source threshold voltage as a function of ambient temperature

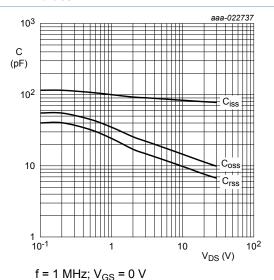


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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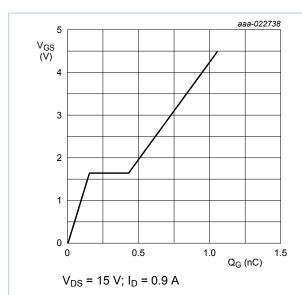


Fig. 14. Gate-source voltage as a function of gate charge; typical values

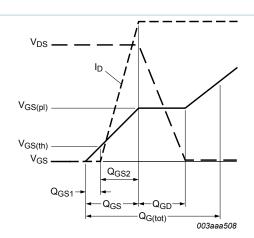


Fig. 15. Gate charge waveform definitions

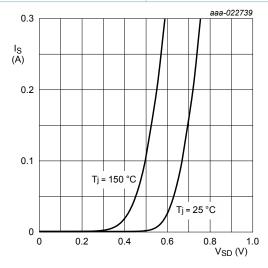
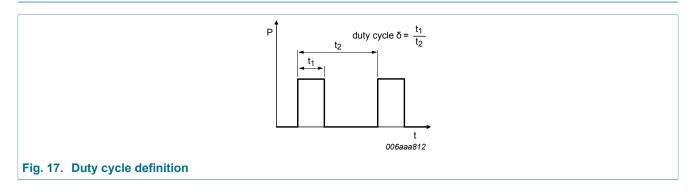


Fig. 16. Source current as a function of source-drain voltage; typical values

 $V_{GS} = 0 V$

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11. Test information



Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

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12. Package outline

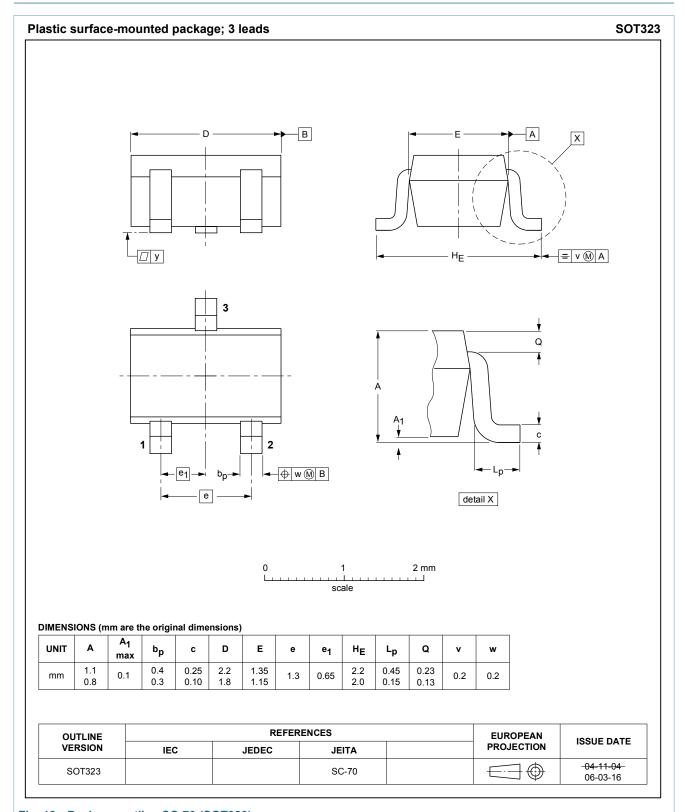
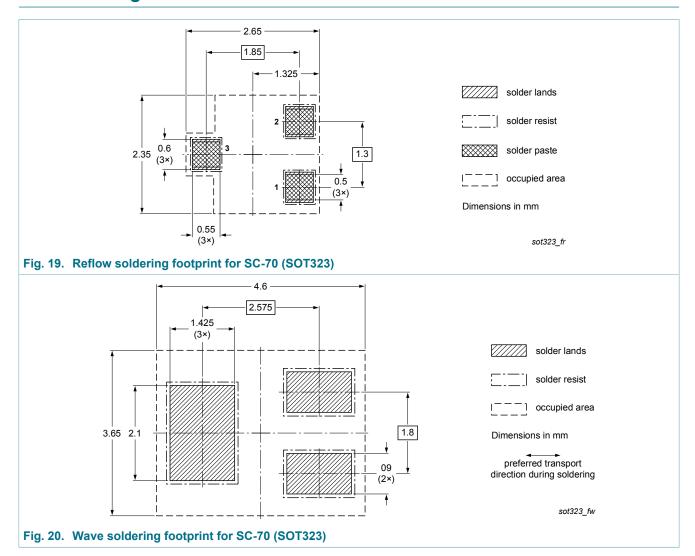


Fig. 18. Package outline SC-70 (SOT323)

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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMF250XNEA v.1	20170317	Product data sheet	-	-

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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